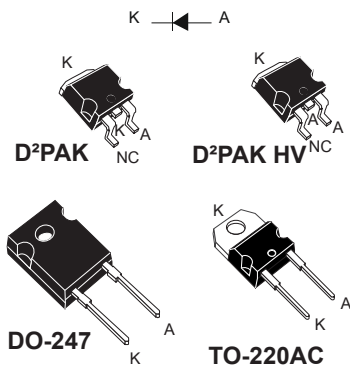



Automotive turbo 2 ultrafast high voltage rectifier



Features

- AEC-Q101 qualified 
- High junction temperature capability
- Ultrafast with soft recovery behavior
- Low reverse current
- Low thermal resistance
- Reduce switching and conduction losses
- PPAP capable
- D²PAK HV creepage distance (anode to cathode) = 5.38 mm min. (with top coating)
- V_{RRM} guaranteed from -40 °C to 175 °C
- ECOPACK^{®2} compliant (DO-247, TO-220AC)

Applications

- Output rectification
- PFC
- UPS
- Air conditioning
- Charging station

Product status link

[STTH30RQ06-Y](#)

Product summary

I_{F(AV)}	30 A
V_{RRM}	600 V
V_F (typ.)	1.45 V
t_{rr} (max.)	30 ns
T_j	-40 °C to +175 °C

Description

The STTH30RQ06-Y has been developed to be used in application requiring a high-voltage secondary rectification for LLC Full Bridge topology.

It is also suited for use in switching power supplies and automotive applications, industrial applications, as rectification, freewheeling and clamping diode.

1 Characteristics

Table 1. Absolute ratings (limiting values, at 25 °C, unless otherwise specified)

Symbol	Parameter		Value	Unit	
V _{RRM}	Repetitive peak reverse voltage	T _j = -40 °C to +175 °C	600	V	
I _{F(RMS)}	Forward rms current		50	A	
I _{F(AV)}	Average forward current $\delta = 0.5$, square wave	T _C = 125 °C	30	A	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms sinusoidal	D ² PAK, D ² PAK HV	180	A
			TO-220AC, DO-247	200	
T _{stg}	Storage temperature range		-65 to +175	°C	
T _j	Operating junction temperature range		-40 to +175	°C	

Table 2. Thermal parameters

Symbol	Parameter	Max. value	Unit
R _{th(j-c)}	Junction to case	0.7	°C/W

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}	-		40	μA
		T _j = 150 °C		-	80	800	
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 15 A	-		2.45	V
		T _j = 150 °C		-	1.15	1.45	
		T _j = 25 °C	I _F = 30 A	-		2.95	
		T _j = 150 °C		-	1.45	1.85	

1. Pulse test: t_p = 5 ms, $\delta < 2\%$

2. Pulse test: t_p = 380 μs, $\delta < 2\%$

To evaluate the conduction losses, use the following equation:

$$P = 1.05 \times I_{F(AV)} + 0.026 \times I_F^2 (RMS)$$

Table 4. Dynamic electrical characteristics

Symbol	Parameter	Test conditions			Min.	Typ.	Max.	Unit
t _{rr}	Reverse recovery time	T _j = 25 °C	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A	-		30	ns	
			I _F = 1 A, V _R = 30 V, di _F /dt = -50 A/μs	-	40	55		
I _{RM}	Reverse recovery current	T _j = 125 °C	I _F = 30 A, V _R = 400 V, di _F /dt = -200 A/μs	-	8	11	A	
Q _{RR}	Reverse recovery charge			-	485	nC		
t _{rr}	Reverse recovery time			-	95	ns		

For more information, please refer to the following application notes related to the power losses:

- AN604: Calculation of conduction losses in a power rectifier
- AN4021: Calculation of reverse losses in a power diode

1.1 Characteristics (curves)

Figure 1. Average forward power dissipation versus average forward current (square waveform)

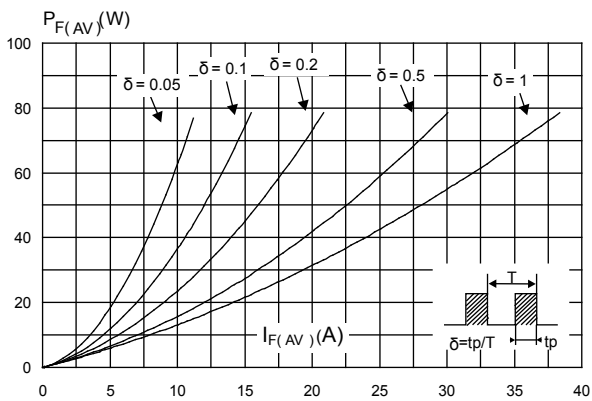


Figure 2. Average forward power dissipation versus average forward current (sinusoidal waveform)

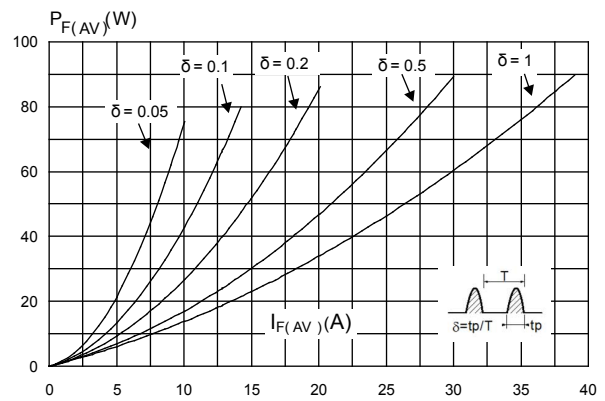


Figure 3. Forward voltage drop versus forward current (typical values)

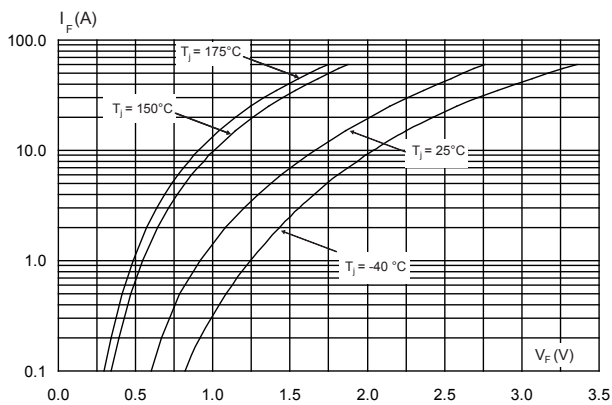


Figure 4. Forward voltage drop versus forward current (maximum values)

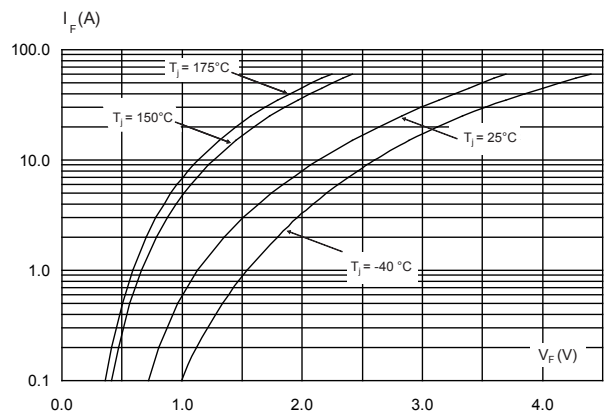


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration

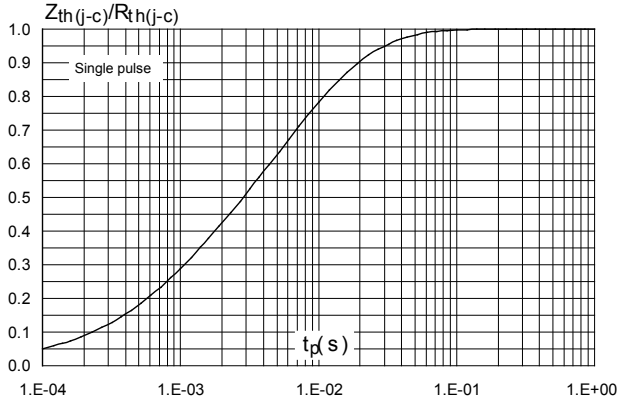


Figure 6. Peak reverse recovery current versus di_F/dt (typical values)

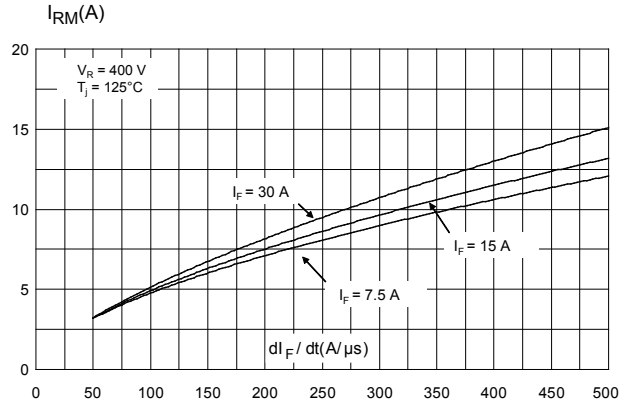


Figure 7. Reverse recovery time versus di_F/dt (typical values)

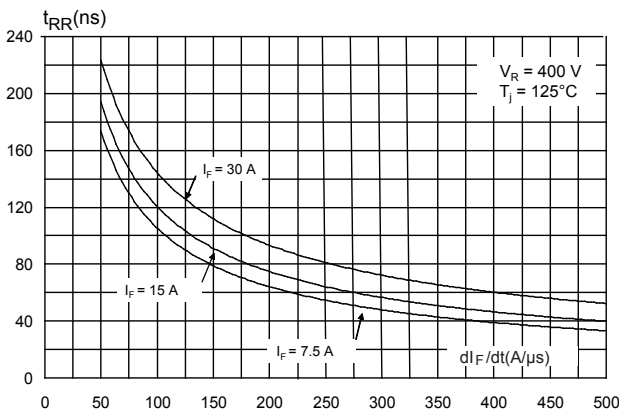


Figure 8. Reverse recovery charges versus di_F/dt (typical values)

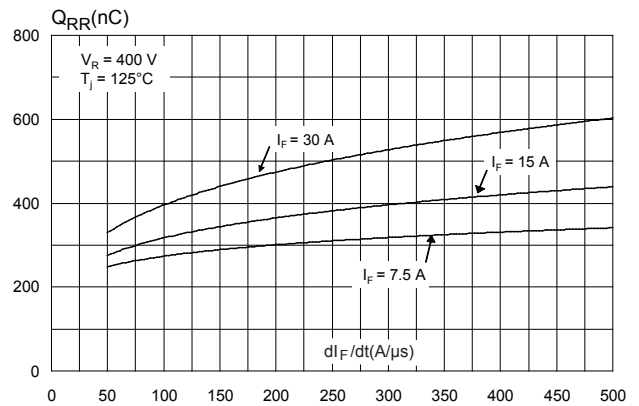


Figure 9. Reverse recovery softness factor versus di_F/dt (typical values)

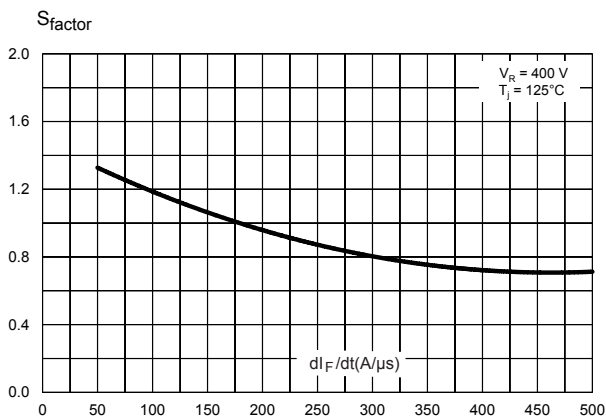


Figure 10. Relative variations of dynamic parameters versus junction temperature

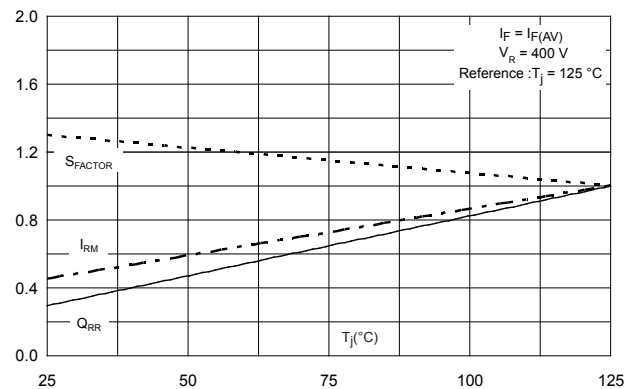


Figure 11. Junction capacitance versus reverse voltage applied (typical values)

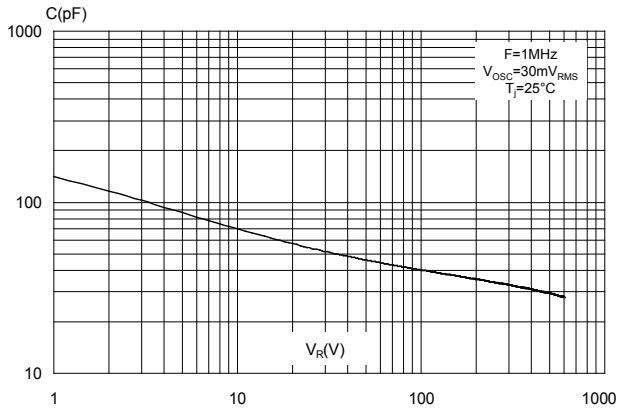


Figure 12. Thermal resistance junction to ambient versus copper surface under tab (typical values, epoxy printed board FR4, $\epsilon_{Cu} = 35 \mu\text{m}$)(D²PAK and D²PAK HV)

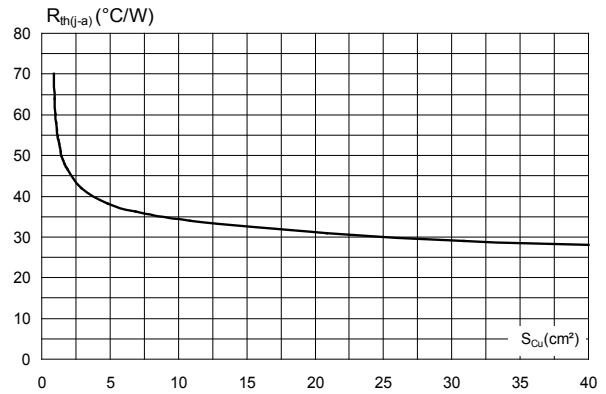


Figure 13. Relative variation of non-repetitive peak surge forward current versus pulse duration (sinusoidal waveform)

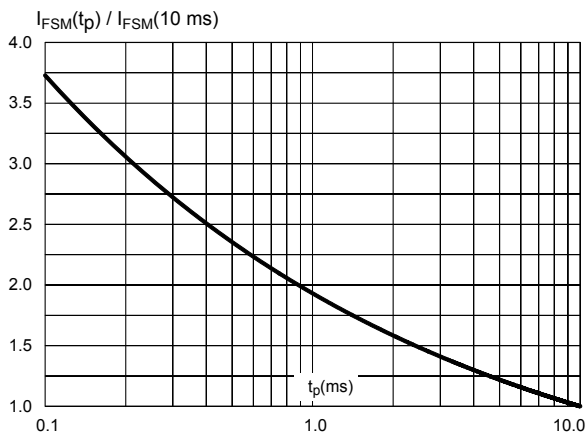
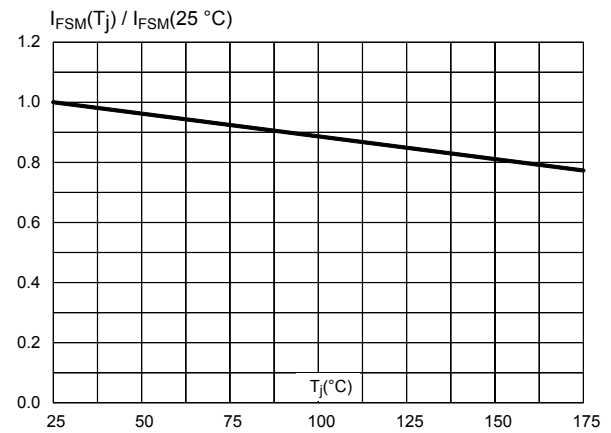


Figure 14. Relative variation of non-repetitive peak surge forward current versus initial junction temperature (sinusoidal waveform)



2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

2.1 DO-247 package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.8 N·m (DO-247)
- Maximum torque value: 1.0 N·m (DO-247)

Figure 15. DO-247 package outline

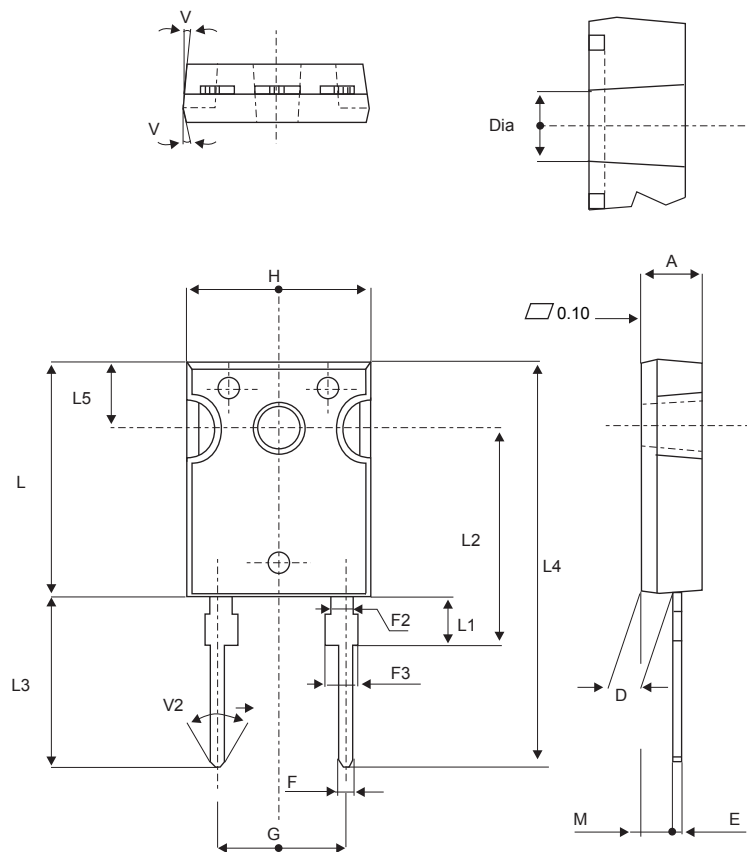


Table 5. DO-247 package mechanical data

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.85	5.15	0.191	0.203
D	2.20	2.60	0.086	0.102
E	0.40	0.80	0.015	0.031
F	1.00	1.40	0.039	0.055
F2	2.00 typ.		0.078 typ.	
F3	2.00	2.40	0.078	0.094
G	10.90 typ.		0.429 typ.	
H	15.45	15.75	0.608	0.620
L	19.85	20.15	0.781	0.793
L1	3.70	4.30	0.145	0.169
L2	18.50 typ.		0.728 typ.	
L3	14.20	14.80	0.559	0.582
L4	34.60 typ.		1.362 typ.	
L5	5.50 typ.		0.216 typ.	
M	2.00	3.00	0.078	0.118
V	5°		5°	
V2	60°		60°	
Dia.	3.55	3.65	0.139	0.143

2.2 D²PAK package information

- Epoxy meets UL94, V0.
- Cooling method: by conduction (C)

Figure 16. D²PAK package outline

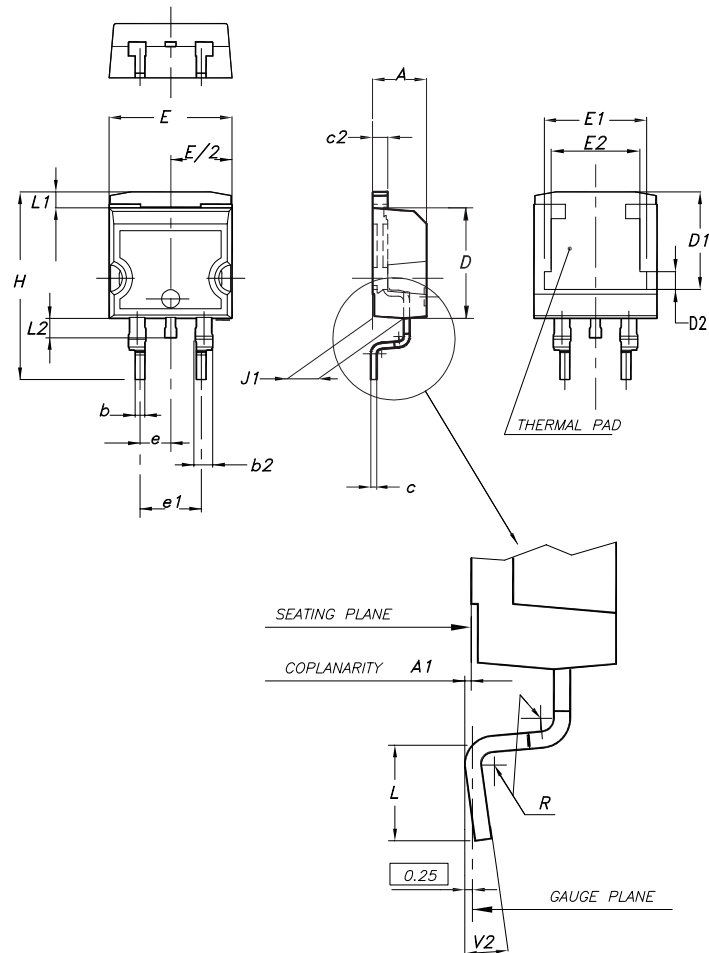
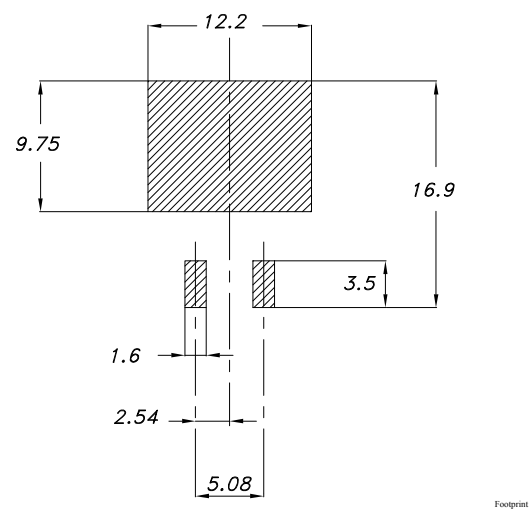


Table 6. D²PAK package mechanical data

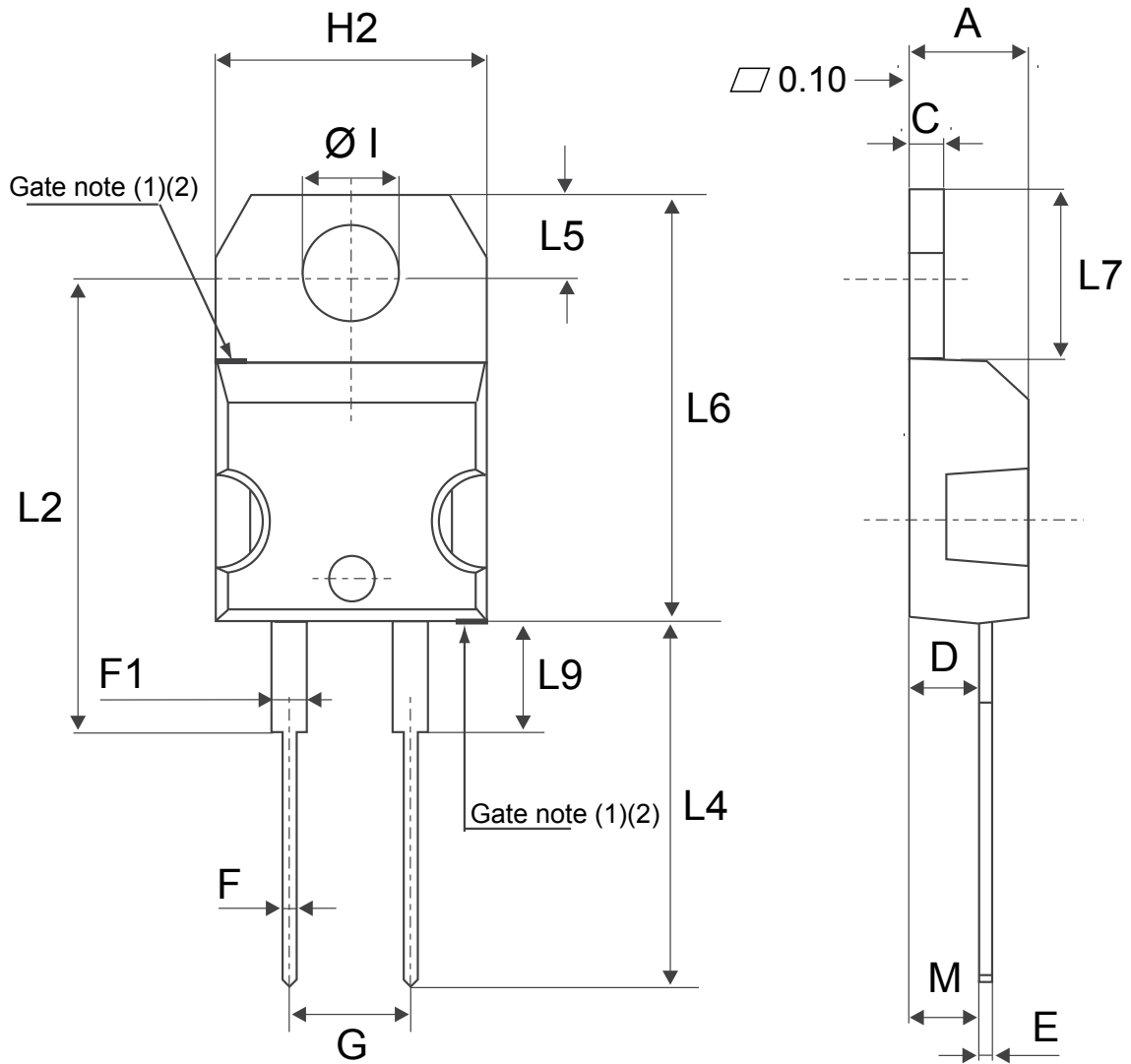
Ref.	Dimensions					
	Millimeters			Inches (for reference only)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.028		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.018		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50	7.75	8.00	0.295	0.305	0.315
D2	1.10	1.30	1.50	0.043	0.051	0.060
E	10.00		10.40	0.394		0.409
E1	8.30	8.50	8.70	0.335	0.343	0.346
E2	6.85	7.05	7.25	0.266	0.278	0.282
e		2.54			0.100	
e1	4.88		5.28	0.190		0.205
H	15.00		15.85	0.591		0.624
J1	2.49		2.69	0.097		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.049		0.055
L2	1.30		1.75	0.050		0.069
R		0.40			0.015	
V2	0°		8°	0°		8°

Figure 17. D²PAK recommended footprint (dimensions are in mm)


2.3 TO-220AC package information

- Epoxy meets UL 94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.55 N·m
- Maximum torque value: 0.70 N·m

Figure 18. TO-220AC package outline



(1) :Max resin gate protusion 0.5 mm

(2) :Resin gate position is accepted in each of the two positions shown on the drawings or their symmetrical

Table 7. TO-220AC package mechanical data

Ref.	Dimensions			
	Millimeters		Inches (for reference only)	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
H2	10.00	10.40	0.393	0.409
L2	16.40 typ.		0.645 typ.	
L4	13.00	14.00	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.60 typ.		0.102 typ.	
Diam	3.75	3.85	0.147	0.151

2.4 D²PAK HV package information

Figure 19. D²PAK high voltage package outline

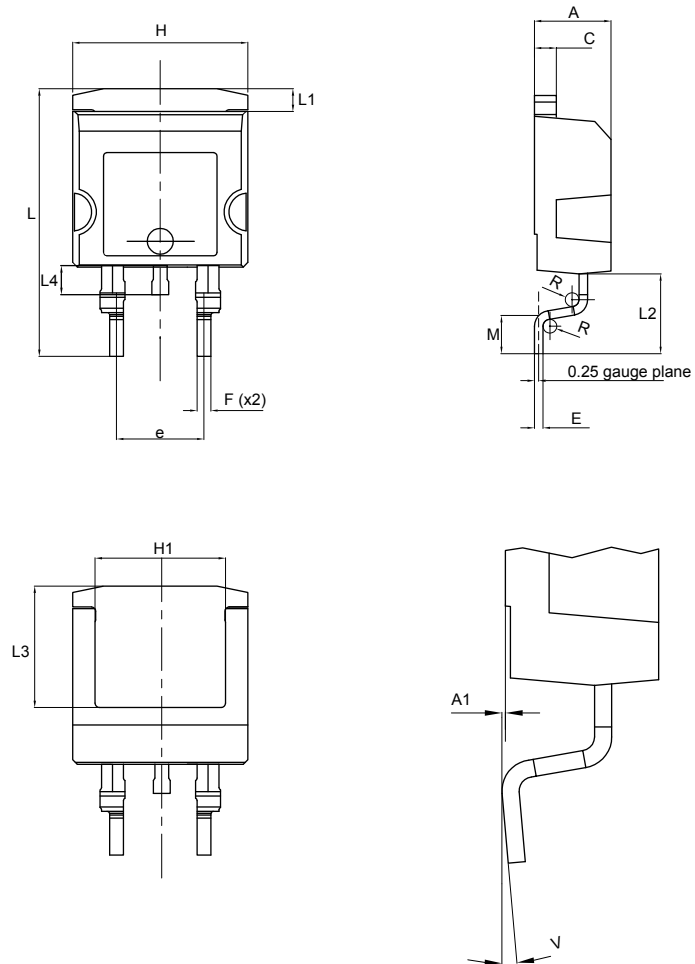
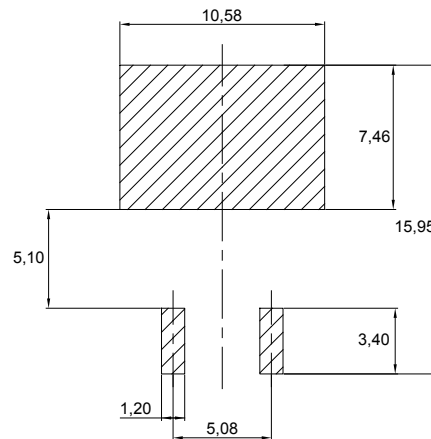


Table 8. D²PAK high voltage package mechanical data

Ref.	Dimensions		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
H	10.00		10.40
H1	7.40		7.80
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.5		1.7
M	2.6		2.9
R	0.20		0.60
V	0°		8°

Figure 20. D²PAK High Voltage footprint in mm



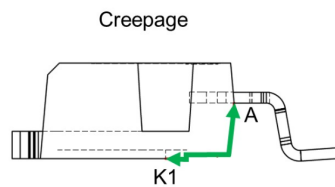
2.4.1 Creepage distance between anode and cathode

Table 9. Creepage distance between anode and cathode

Symbol	Parameter		Value	Unit
Cd _{A-K1}	Minimum creepage distance between A and K1 (with top coating)	D ² PAK HV	5.38	mm
Cd _{A-K2}	Minimum creepage distance between A and K2 (without top coating)		3.48	

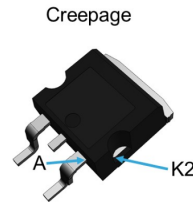
Note: D²PAK HV creepage distance (anode to cathode) = 5.38 mm min. (refer to IEC 60664-1)

Figure 21. Creepage with top coating



Minimum distance between A & K1 = 5.38 mm (with top coating)

Figure 22. Creepage without top coating



Minimum distance between A & K2 = 3.48 mm (without top coating)

3 Ordering information

Table 10. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH30RQ06GY-TR	STTH30RQ06GY	D ² PAK	1.48 g	1000	Tape and reel
STTH30RQ06DY	STTH30RQ06DY	TO-220AC	1.86 g	50	Tube
STTH30RQ06WY	STTH30RQ06WY	DO-247	4.40 g	30	Tube
STTH30RQ06G2Y-TR	TH30RQ06G2Y	D ² PAK HV	1.48 g	1000	Tape and reel

Revision history

Table 11. Document revision history

Date	Revision	Changes
12-Jun-2017	1	Initial release.
09-Oct-2018	2	Added D ² PAK HV package.
20-Nov-2018	3	Updated Features and Table 9 . Creepage distance between anode and cathode. added Figure 22 . Creepage without top coating.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries (“ST”) reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST’s terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers’ products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2018 STMicroelectronics – All rights reserved

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9